



PRODUCT NAME : 2SA1317 PNP General Purpose Transistor

PRICE : Rs 15.00

SKU : RM2138

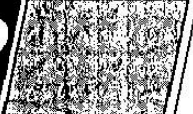
DESCRIPTION

Features

- Collector-Emitter Volt (V_{ce0}): 50V
- Collector-Base Volt (V_{cbo}): 60V
- Collector Current (I_c): 0.2A
- h_{fe} : 100-800 @ 1mA
- Power Dissipation (P_{tot}): 300mW
- Current-Gain-Bandwidth (f_{total}): 200MHz
- Type: PNP



Ordering number: EN1599A

SANYO	No.1599A	2SA1317/2SC3330
		PNP/ NPN Epitaxial Planar Silicon Transistors
AF Amp Applications		

Use

. Capable of being used in the low frequency to high frequency range.

Features

. Large current capacity and wide ASO.

(): 2SA1317

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)60	V
Collector to Emitter Voltage	V _{CEO}	(-)50	V
Emitter to Base Voltage	V _{EB0}	(-)6	V
Collector Current	I _C	(-)200	mA
Collector Current (Pulse)	I _{CP}	(-)400	mA
Collector Dissipation	P _C	300	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

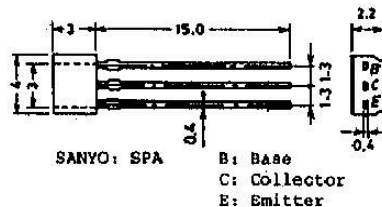
			min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} =(-)40V, I _E =0			(-)0.1	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} =(-)5V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)6V, I _C =(-)1mA	100*		800*	
			(100)		(560)	
Gain-Bandwidth Product	h _{FE} (2)	V _{CE} =(-)6V, I _C =(-)0.1mA		70		
	f _T	V _{CE} =(-)6V, I _C =(-)10mA		200		MHz
Output Capacitance	C _{ob}	V _{CB} =(-)6V, f=1MHz		3.0		pF
				(4.0)		

Continued on next page.

* The 2SA1317/2SC3330 are classified by 1mA h_{FE} as follows:

2SA1317	100	R	200	140	S	280	200	T	400	280	U	560			
2SC3330	100	R	200	140	S	280	200	T	400	280	U	560	400	V	800

Case Outline 2033
(unit:mm)



Specifications and information herein are subject to change without notice.

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